

QSI LASER DIODE SPECIFICATIONS

Customer :

Tentative

Model : QL90V8SM-7

Signature of Approval

Approved by _____

Checked by _____

Issued by _____

Approval by Customer



QSI Co., Ltd.

17, Cheonheung 8gil, Sungger-eup, Seobuk-gu,
Cheonan-city, Chungnam, Korea

WWW.QSILaser.com

QL90V8SM-7

InGaAs Laser Diode

Quantum Semiconductor International Co., Ltd.

Ver.2 2018

◆ OVERVIEW

QL90V8SM-7 is a MOCVD grown 905nm band *InGaAs* laser diode with quantum well structure.

It's an attractive light source, with a optical peak output power of 21W (pulse operation) for industrial optical module and sensor applications.

◆ APPLICATION

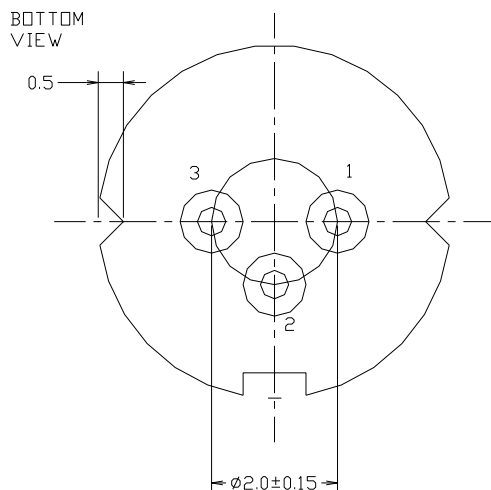
- Laser Range Finder (LRF) , Automotive applications

◆ FEATURES

- Light Output : $\lambda_p = 905 \text{ nm}$
- Optical Power Output : 21W (Pulse Operation)
- Package Type : TO-18 (5.6mm ϕ)

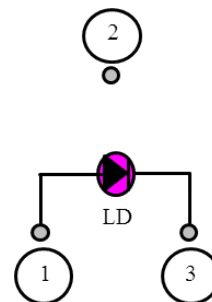
◆ ELECTRICAL CONNECTION

Bottom View



Pin Configuration

M	1: anode (+)	3: Cathode (-)
---	--------------	----------------



◆ ABSOLUTE MAXIMUM RATING (Short time Operation, Tc=25°C)

Items	Symbols	Values	Unit
Peak Output Power	$P_{\max}$	30	W
Forward Current	I_F	10	A
Pulse width (FWHM)	t_p	100	ns
Duty Ratio	dr	0.1	%
Reverse Voltage	V_R	3	V
Operating Temperature	T_{opr}	-40 ~ 85	°C
Storage Temperature	T_{stg}	-40 ~125	°C

◆ ELECTRICAL and OPTICAL CHARACTERISTICS at Tc=25°C

Items	Symbols	Min.	Typ.	Max.	Unit
Optical Output Power	P_{op}	17	21	-	W
Emission Wavelength	λ_p	895	905	915	nm
Spectral Width (FWHM)	$\Delta\lambda$	-	5	-	nm
Threshold Current	I_{th}	-	-	0.5	A
Operating Current	I_{op}	-	7	-	A
Operating Voltage	V_{op}	-	-	12	V
Beam Divergence	$\theta_{ }$	-	10	-	deg
	$\theta_{\perp}$	-	28	-	deg

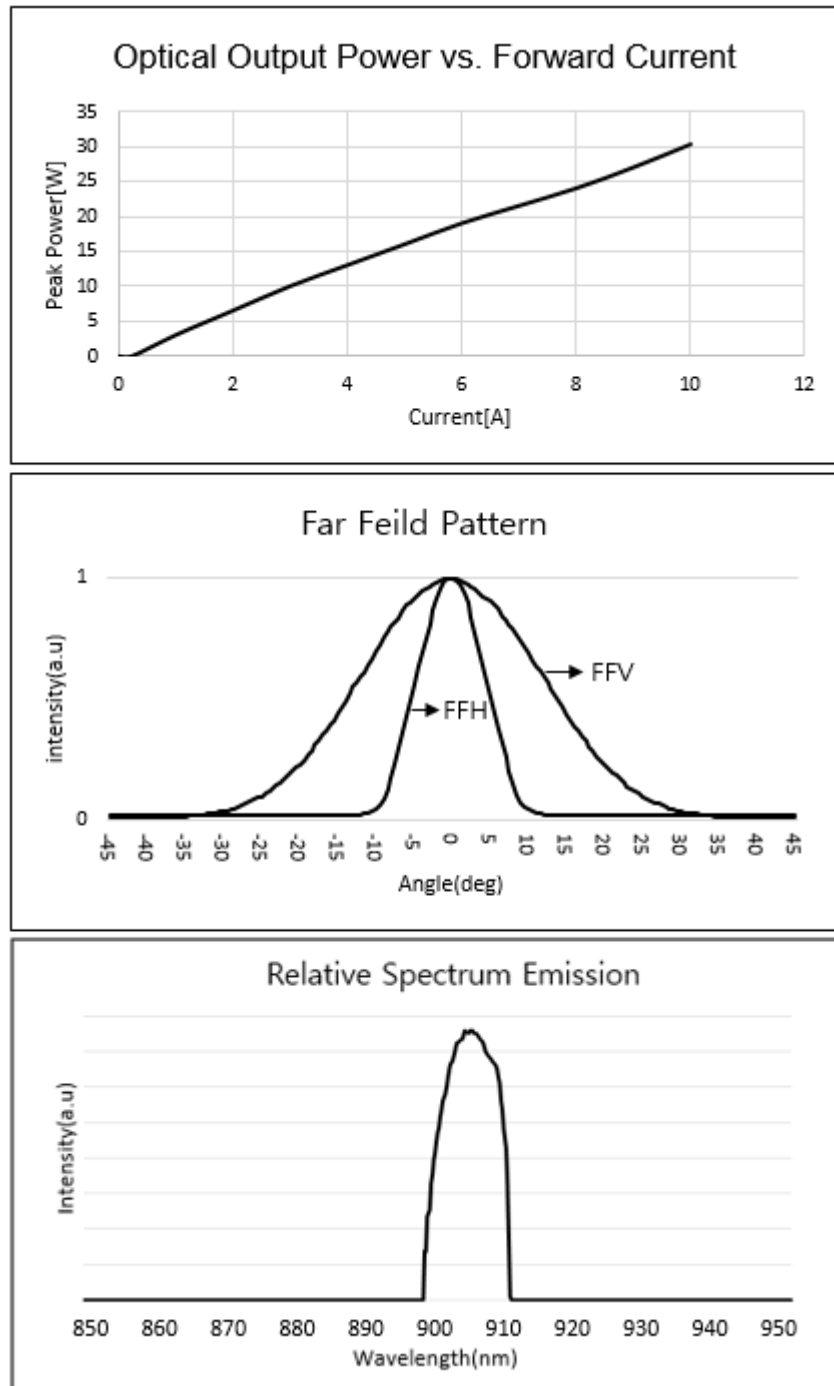
*Operating condition - Pulse Width $P_w = 100\text{nsec}$, Repetition Frequency $Fr = 1\text{kHz}$, Duty Ratio $Dr = 0.01\%$

◆ CHIP CHARACTERISTICS

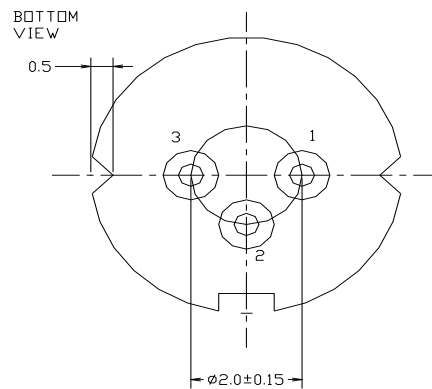
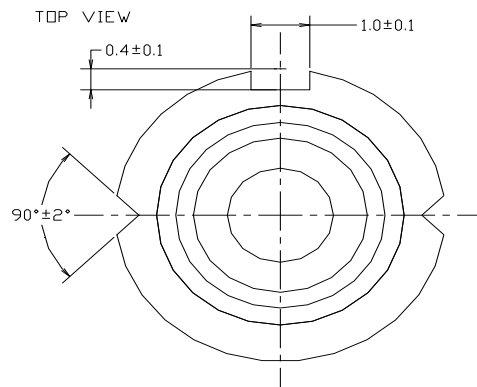
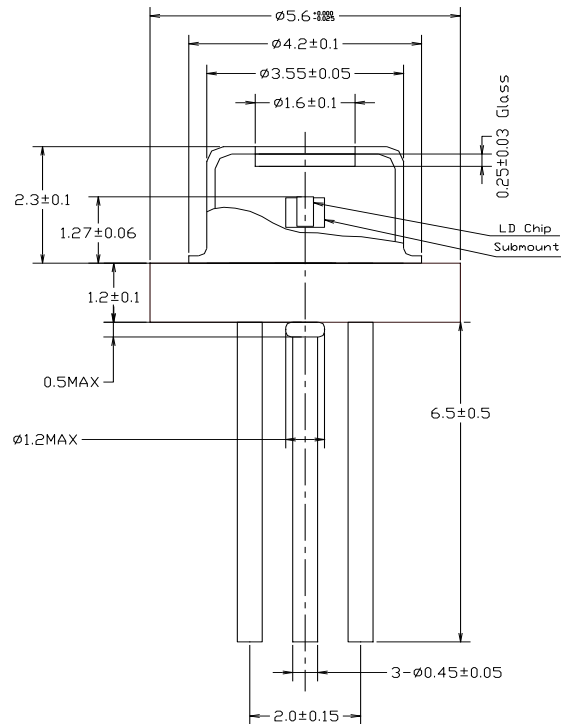
Size	symbols	Min.	Type.	Max.	Unit
Aperture Size	$W \times H$	—	75×10	—	μm^2

The above product specifications are subject to change without notice.

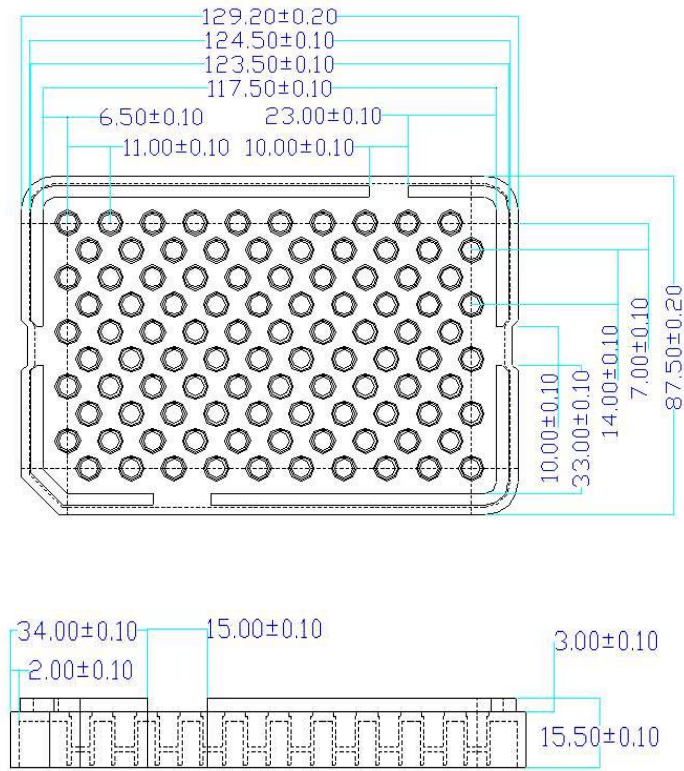
◆ E-O CHARACTERISTICS at $T_c=25^{\circ}\text{C}$



◆ PACKAGE DIMENSION



◆PACKING



*Precautions

1. Operating the laser diode exceeding the Maximum rating conditions, even momentarily, may cause device failure or safety hazard.
2. It is highly recommended to prevent ESD or surge current from the laser diode. ESD is the primary cause of unexpected device failure.
3. When the laser diode is in operation, looking into laser beam directly by naked eyes may cause severe damage to human eyes.